

HiPerFET™

Power MOSFETs

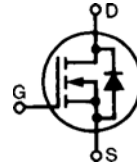
Q Class

IXFH/IXFT12N100Q
IXFH/IXFT10N100Q

V_{DSS}	I_{D25}	$R_{DS(on)}$
1000 V	12 A	1.05 Ω
1000 V	10 A	1.20 Ω

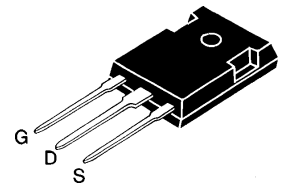
$t_{rr} \leq 250$ ns

N-Channel Enhancement Mode
Avalanche Rated
Low Q_g , High dv/dt

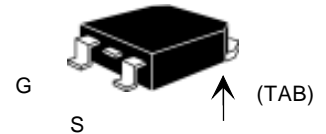


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	12N100Q	12 A
		10N100Q	10 A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	12N100Q	48 A
		10N100Q	40 A
I_{AR}	$T_C = 25^\circ\text{C}$	12N100Q	12 A
		10N100Q	10 A
E_{AR}	$T_C = 25^\circ\text{C}$	30	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2\ \Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-247 AD	6 g
		TO-268	4 g

TO-247 AD (IXFH)



TO-268 (D3) (IXFT)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 3\text{ mA}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4\text{ mA}$	2.5		5.5 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$		50 μA
		$T_J = 125^\circ\text{C}$		1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$	12N100Q		1.05 Ω
		10N100Q		1.20 Ω

Features

- IXYS advanced low Q_g process
- Low gate charge and capacitances
 - easier to drive
 - faster switching
- International standard packages
- Low $R_{DS(on)}$
- Unclamped Inductive Switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

- Easy to mount
- Space savings
- High power density

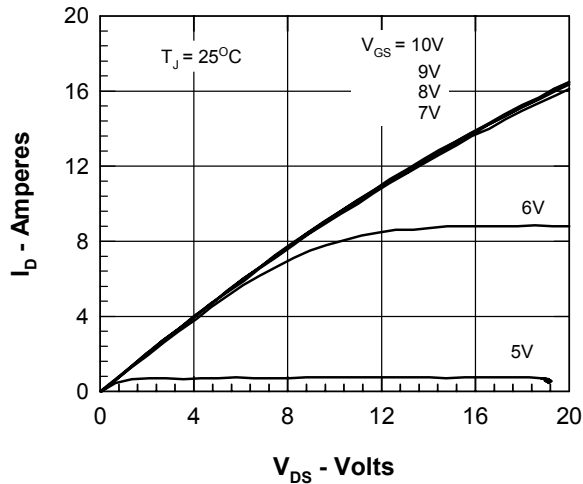


Figure 1. Output Characteristics at 25°C

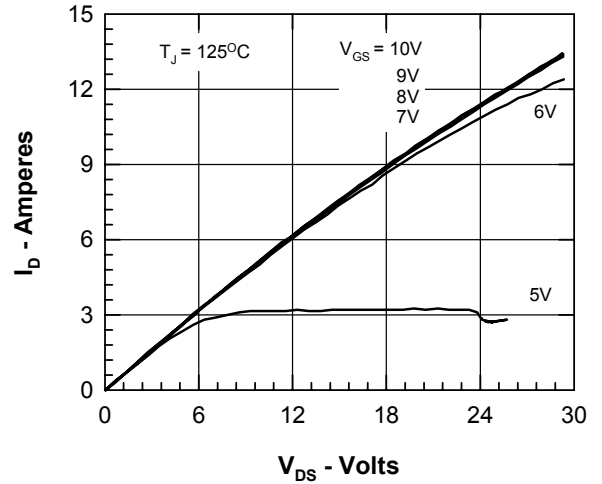


Figure 2. Output Characteristics at 125°C

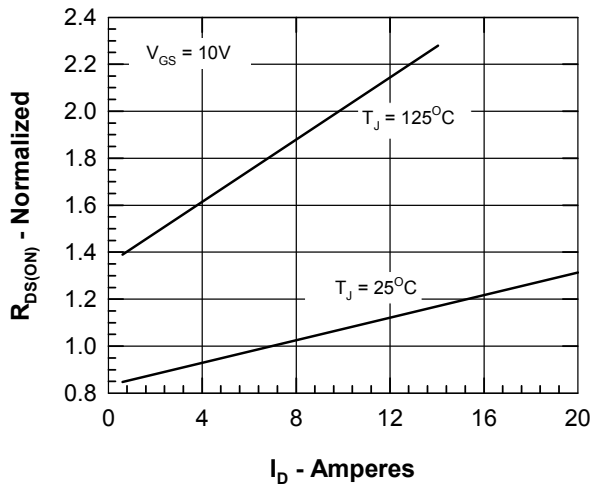


Figure 3. $R_{DS(on)}$ normalized to value at $I_D = 12A$

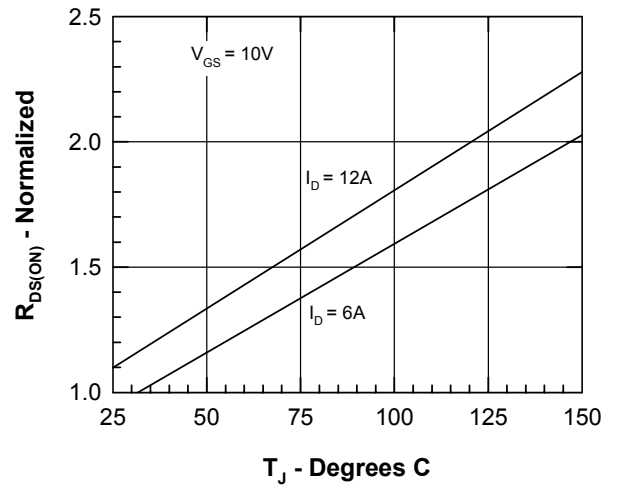


Figure 4. $R_{DS(on)}$ normalized to value at $I_D = 12A$

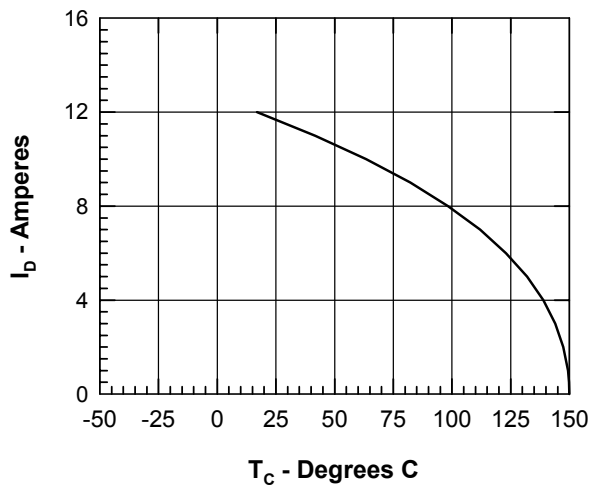


Figure 5. Drain Current vs. Case Temperature

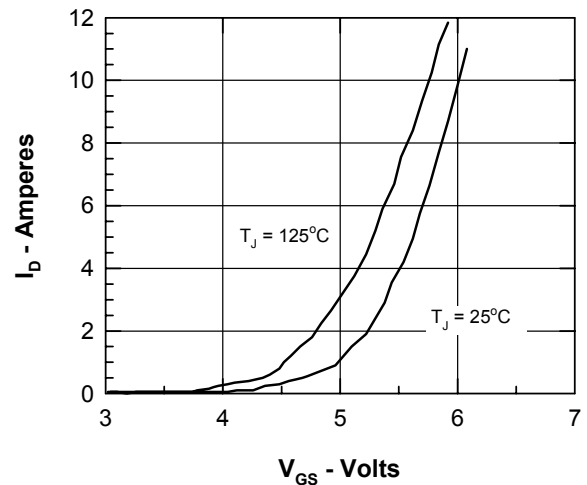


Figure 6. Admittance Curves

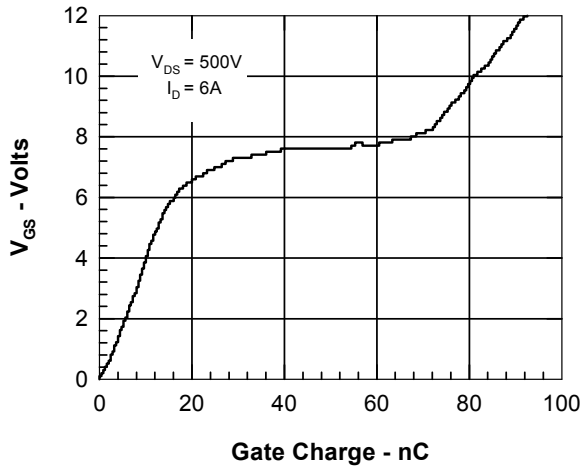


Figure 7. Gate Charge

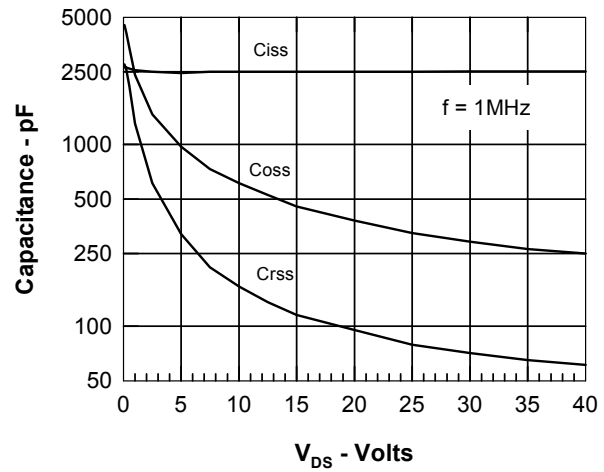


Figure 8. Capacitance Curves

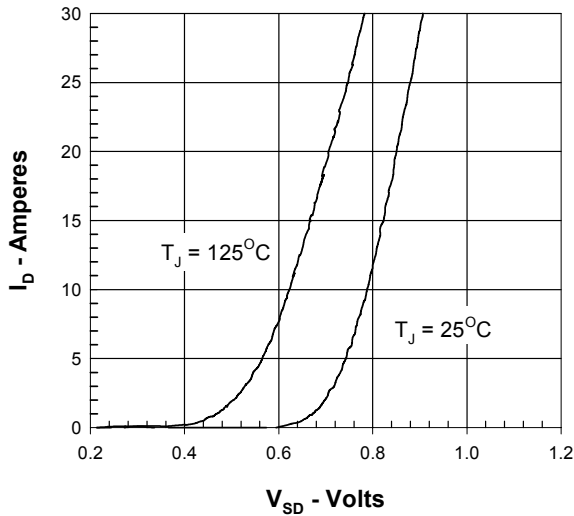


Figure 9. Source Current vs. Source to Drain Voltage

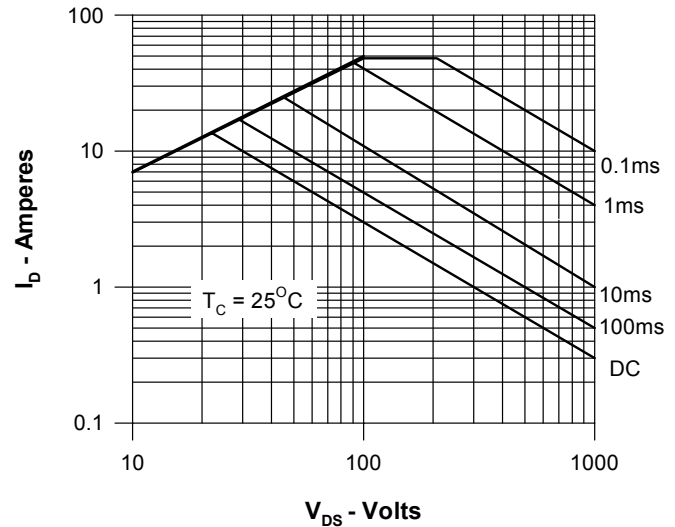


Figure 10. Forward Bias Safe Operating Area

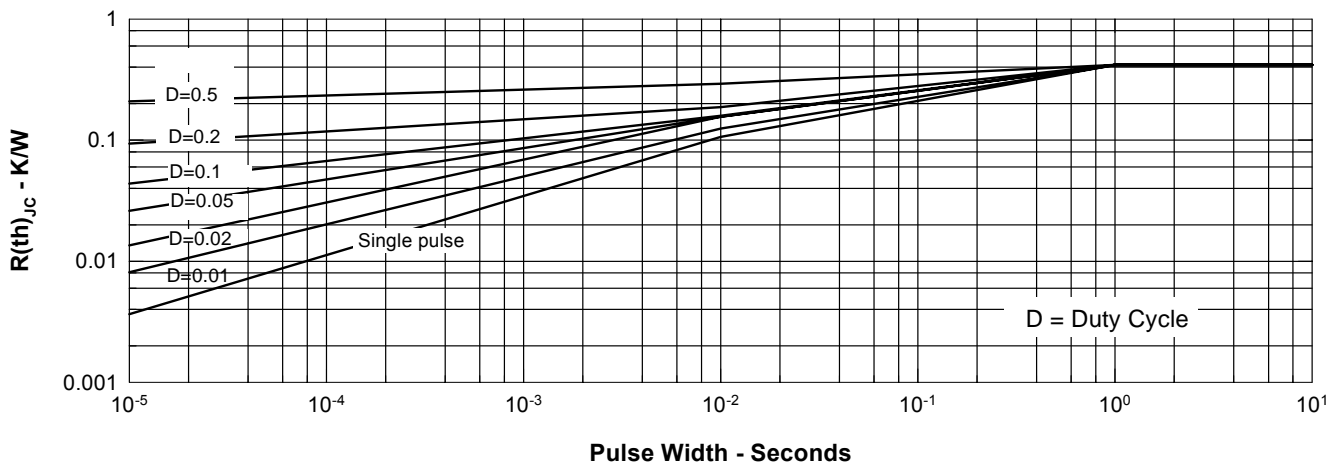


Figure 11. Transient Thermal Resistance

IXYS reserves the right to change limits, test conditions, and dimensions.

 IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	



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